

GD103SD

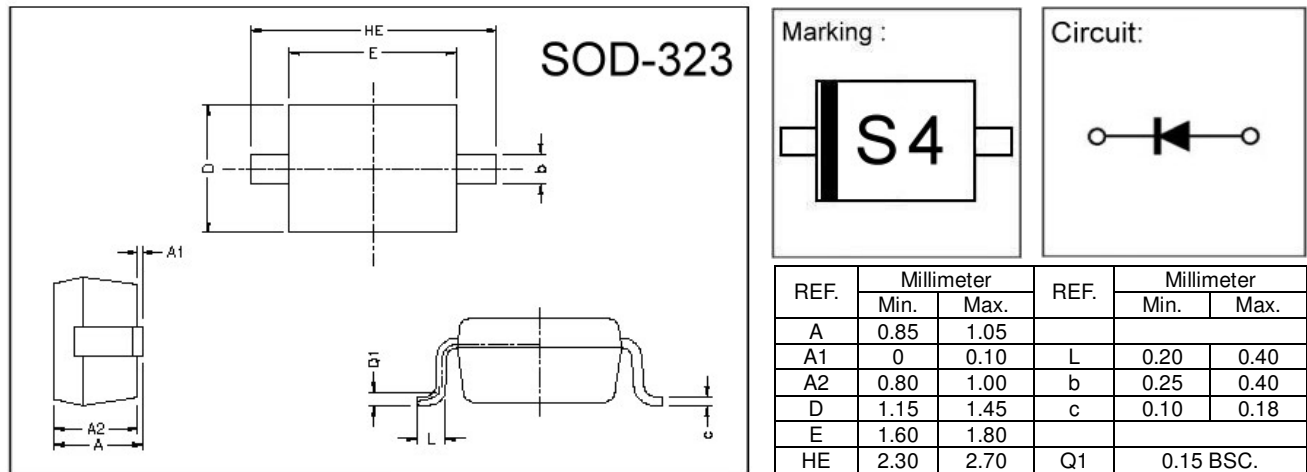
SURFACE MOUNT, SCHOTTKY BARRIER DIODE

VOLTAGE 40V, CURRENT 350mA

Description

The GD103SD is designed for low forward voltage drop, guard ring construction for transient protection, negligible reverse recovery time and low reverse capacitance.

Package Dimensions



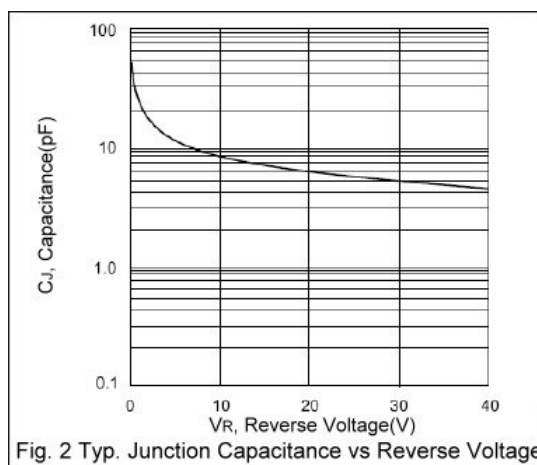
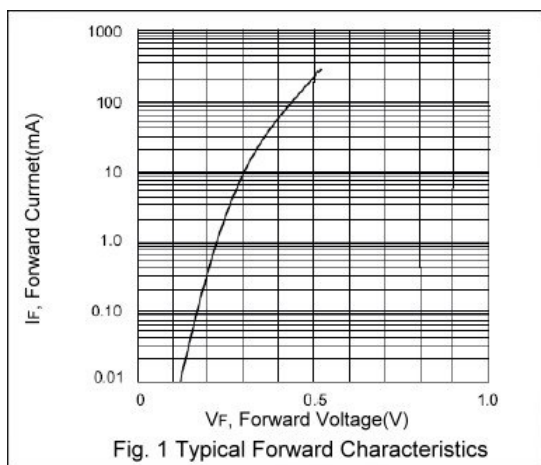
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Storage Temperature	Tstg	-65 ~ +125	°C
Peak Repetitive Reverse Voltage	VR	40	V
RMS Reverse Voltage	VR(RMS)	28	V
Forward Continuous Current	IF	350	mA
Repetitive Peak Forward Current(t ≤ 1.0s)	IFRM	1.5	A
Thermal Resistance Junction to Ambient	RθJA	625	°C/W
Total Power Dissipation at Ta = 25°C	PD	225	mW

Characteristics at Ta = 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V(BR)R	40	-	-	V	IR=10μA
Forward Voltage	VF(1)	-	-	370	mV	IF=20mA
	VF(2)	-	-	600	mV	IF=200mA
Reverse Leakage Current	IR	-	-	5.0	μA	VR=30V
Total Capacitance	CT	-	5.0	-	pF	VR=0V, f=1MHz
Reverse Recover Time	Trr	-	10	-	ns	IF=IR=200mA, IR(Rec)=20mA, RL=100Ω

Characteristics Curve



Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165